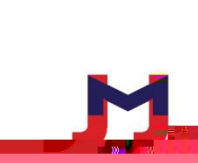
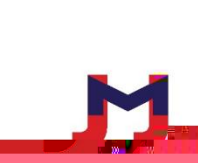
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($_{vj}$=25 unless otherwise specified)

$_{F}$	Diode forward voltage	$_{F}$=30A	-	1.7	-	V
		$_{F}$=30A, $_{vj}$=175	-	1.4	-	V
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=30A d $_{F}$/d =-550A/μs	-	105	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	16	-	A
$_{rr}$	Diode reverse recovery charge		-	876	-	nC
$_{rr}$	Diode reverse recovery time	$_{R}$=400V $_{F}$=30A d $_{F}$/d =-550A/μs $_{vj}$=175	-	171	-	ns
$_{rrm}$	Diode peak reverse recovery current		-	26	-	A
$_{rr}$	Diode reverse recovery charge		-	2650	-	nC

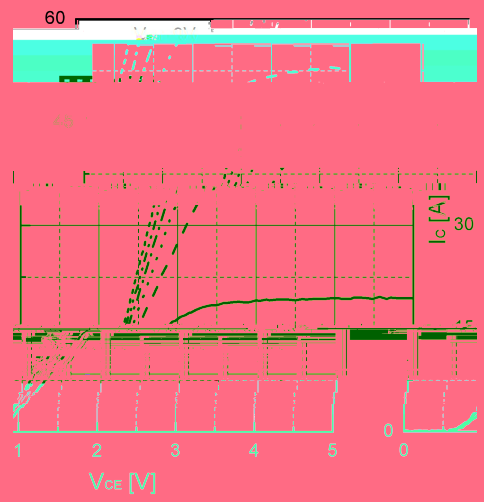


Fig 1. Typical output characteristic ($_{vj}$=25)

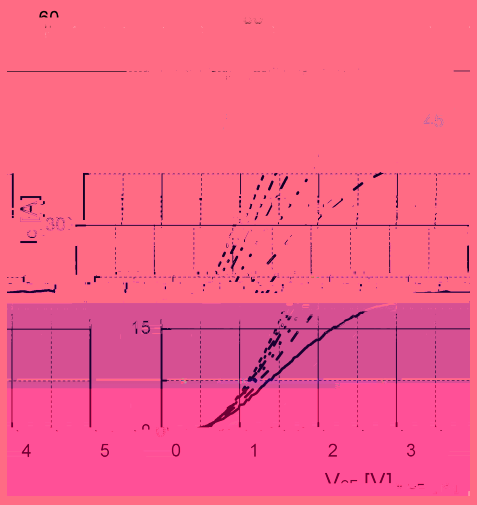


Fig 2. Typical output characteristic($_{vj}$=175)

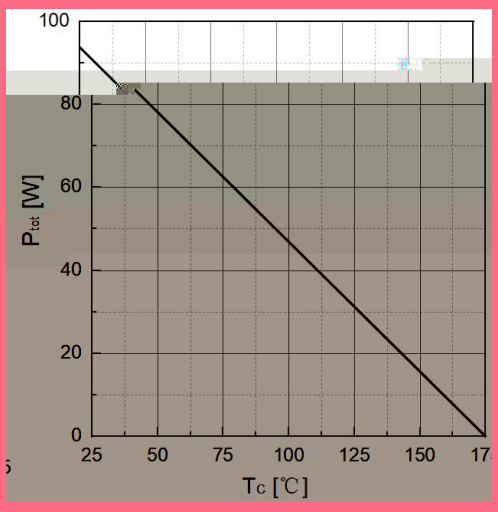


Fig 3. Power dissipation as a function of

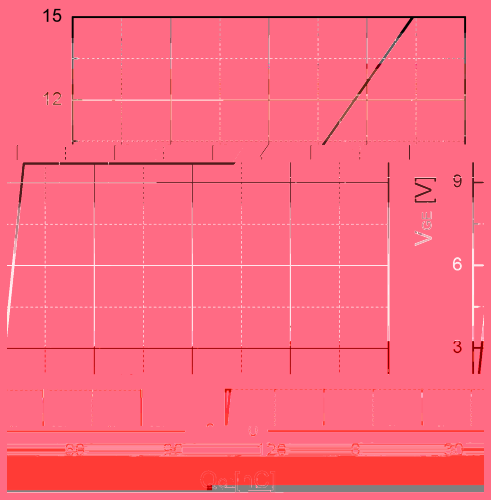


Fig 4. Typical Gate charge

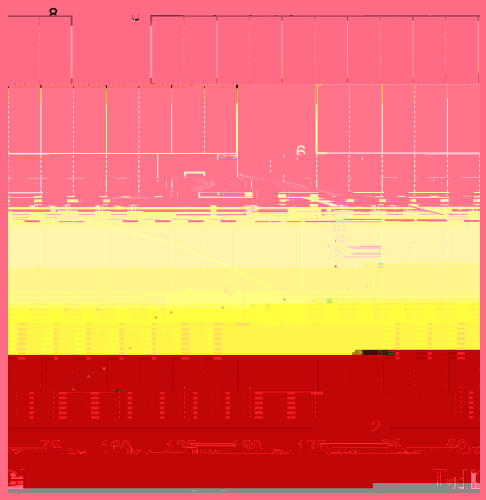


Fig 5. Typical $_{GE(th)}$ as a function of $_{vj}$ ($_{C}$=1mA)

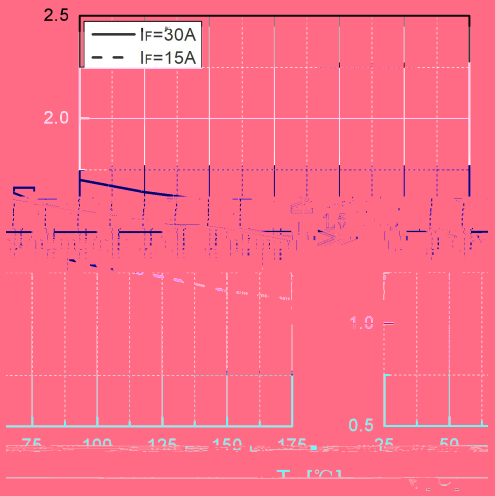


Fig 6. Typical $_{F}$ as a function of $_{vj}$

A d c f a c ed a d bec e a d ca e .

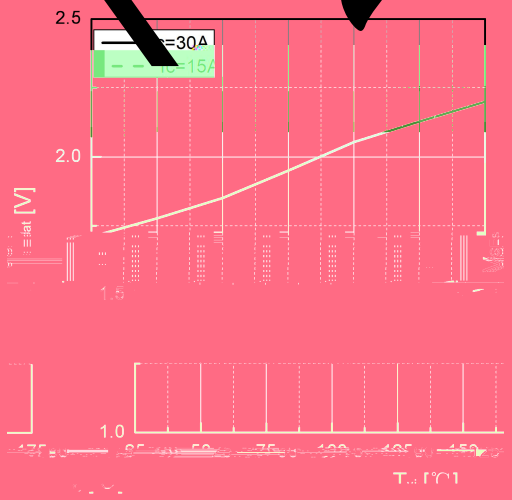


Fig 7. Typical $_{CEsat}$ as a function of $_{vj}$

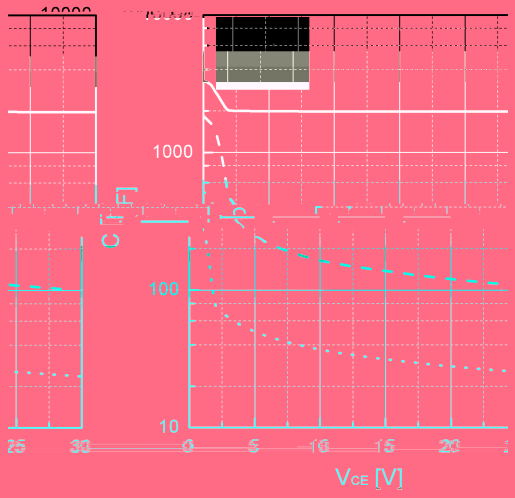


Fig 13. Typical capacitance as a function of $_{CE}$ (f=1Mhz, $_{GE}$=0V)

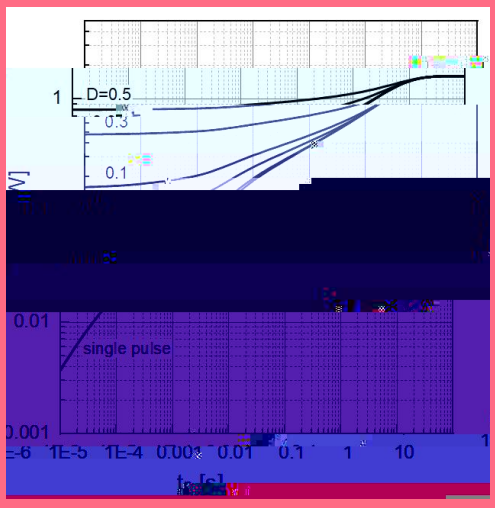


Fig 14. Transient thermal impedance, IGBT

Dimensions

Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50	-	4.90	0.177	-	0.193
B	0.74	0.80	0.83			

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Date	Revision	Changes
2023-12-27	Rev 1.0	Release of the datasheet
2025-03-09	Rev 1.1	Character update
2026-06-24	Rev 1.2	Update thermal

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